

Silicon Diode

FESB8DT

Fast Efficient Rectifier

200V / 8A

DATASHEET

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OEM – General Semiconductor

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NEW PRODUCT

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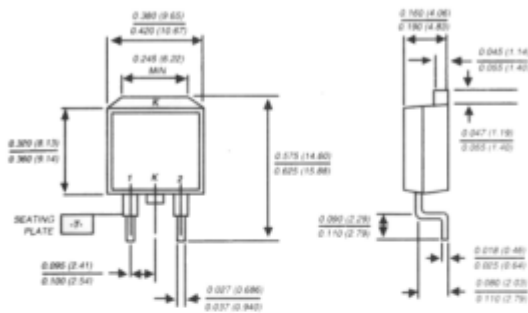
NEW PRODUCT

FESB8AT THRU FESB8JT

FAST EFFICIENT PLASTIC RECTIFIER

Reverse Voltage - 50 to 600 Volts Forward Current - 8.0 Amperes

TO-263AB



Dimensions in inches and (millimeters)

FEATURES

- ◆ Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- ◆ Glass passivated chip junction
- ◆ Low leakage, high voltage
- ◆ High surge current capability
- ◆ Superfast recovery time, for high efficiency
- ◆ High temperature soldering in accordance with CECC 802 / Reflow guaranteed



MECHANICAL DATA

Case: JEDEC TO-263AB molded plastic body
Terminals: Plated lead solderable per MIL-STD-750, Method 2026
Polarity: As marked
Mounting Position: Any
Weight: 0.08 ounce, 2.24 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

	SYMBOLS	FESB 8AT	FESB 8BT	FESB 8CT	FESB 8DT	FESB 8FT	FESB 8GT	FESB 8HT	FESB 8JT	UNITS
Maximum recurrent peak reverse voltage	V _{RRM}	50	100	150	200	300	400	500	600	Volts
Maximum RMS voltage	V _{RMS}	35	70	105	140	210	280	350	420	Volts
Maximum DC blocking voltage	V _{DC}	50	100	150	200	300	400	500	600	Volts
Maximum average forward rectified current at T _C =100°C	I _{F(AV)}	8.0								Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	125.0								Amps
Maximum instantaneous forward voltage at 8.0A	V _F	0.95		1.3		1.5				Volts
Maximum DC reverse current at rated DC blocking voltage at T _C =25°C T _C =100°C	I _R	10.0 500.0								μA
Maximum reverse recovery time (NOTE 1)	t _{rr}	35.0			50.0					ns
Typical junction capacitance (NOTE 2)	C _J	85.0				50.0				pF
Typical thermal resistance (NOTE 3)	R _{θJC}	3.0								°C/W
Operating junction and storage temperature range	T _J , T _{STG}	-65 to +150								°C

NOTES:

- (1) Reverse recovery test conditions: I_F=0.5A, I_R=1.0A, I_{rr}=0.25A
- (2) Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts
- (3) Thermal resistance from junction to case mounted on heatsink

RATINGS AND CHARACTERISTIC CURVES FESB8AT THRU FESB8JT

FIG. 1 - MAXIMUM FORWARD CURRENT DERATING CURVES

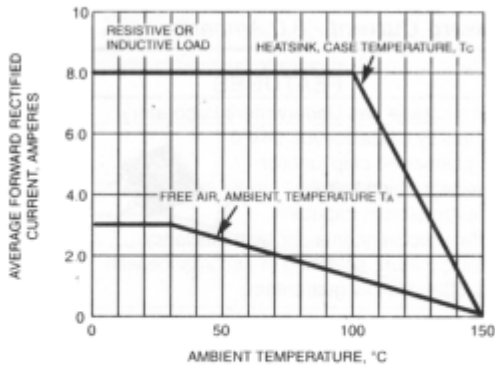


FIG. 2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

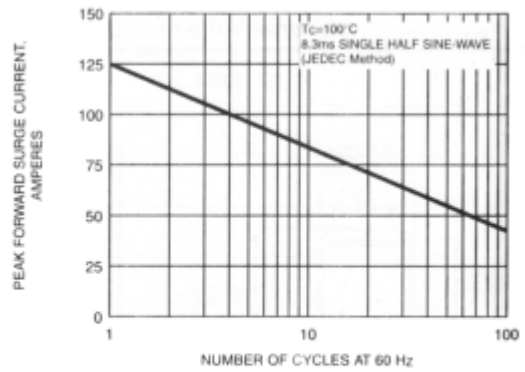


FIG. 3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

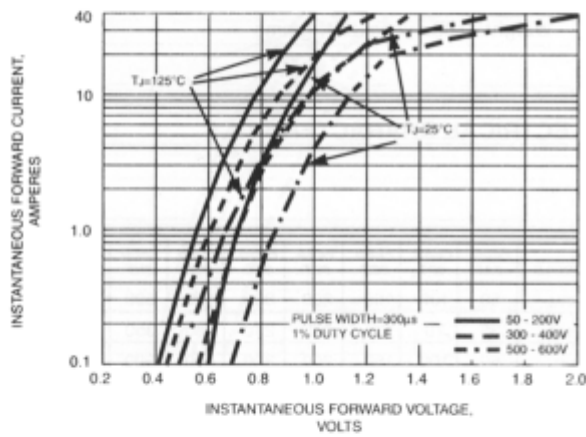


FIG. 4 - TYPICAL REVERSE LEAKAGE CHARACTERISTICS

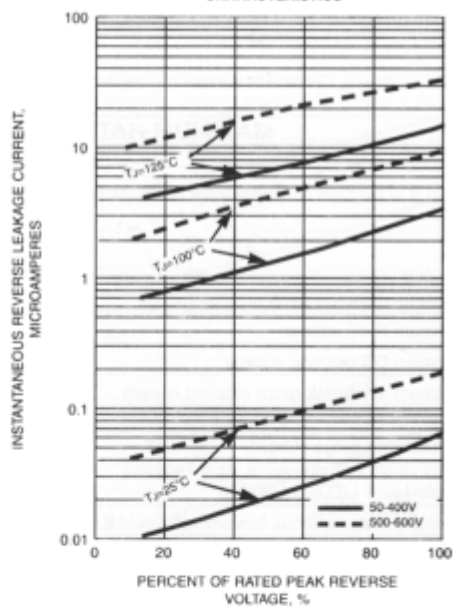


FIG. 5 - TYPICAL JUNCTION CAPACITANCE

